

Title (en)

Anodizing apparatus, anodizing system, substrate processing apparatus and method, and substrate manufacturing method

Title (de)

Vorrichtung und System zur anodischen Oxidation, Vorrichtung und Verfahren zur Bearbeitung von Substraten, und Substratherstellungsverfahren

Title (fr)

Appareil et système d'oxydation anodique, appareil et méthode de traitement de substrats, et méthode de fabrication de substrats

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Application

EP 00302428 A 20000324

Priority

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Abstract (en)

This invention is to reduce the influence of a gas generated by an anodizing reaction. A silicon substrate (101) to be processed is horizontally held. A negative electrode (129) is arranged on the upper side of the silicon substrate (101), and a positive electrode (114) is brought into contact with the lower surface of the silicon substrate (101). The space between the negative electrode (129) and the silicon substrate (101) is filled with an HF solution (132). The negative electrode (129) has a number of degassing holes (130) to prevent a gas generated by the anodizing reaction from staying on the lower side of the negative electrode (129). <IMAGE>

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H01L 21/00

IPC 8 full level

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